

of:

sealing the front surface of a wafer having the front and rear surfaces and having formed a plurality of semiconductor chips on the front surface with resin material;

a first marking the position information corresponding to each chip in the region of each chip at the rear surface of said wafer;

conducting electrical test to each chip;

a second marking the result of said electrical test corresponding to each chip in the region of each chip at the rear surface of said wafer; and

dicing the wafer into each chip.

2. A method of manufacturing wafer level semiconductor device comprising:

sealing the front surface of a wafer having the front and rear surfaces and having formed a plurality of semiconductor chips on the front surface thereof with resin material;

conducting electrical test to each chip;

marking in the region of each chip at the rear surface of said wafer, the position information corresponding to each chip and the result of said electrical test; and

dicing the wafer into each chip.

3. A method of manufacturing wafer level semiconductor as claimed in claim 1 or 2, wherein the circuit surface of said wafer and the opposite surface thereof are sealed with resin material and said position information and result of electrical test are marked in the region of each chip on the surface.